

Amendments to the Specification:

Please replace the paragraph bridging pages 14 and 15 with the following amended paragraph:

First, a gate line 402 is formed on a substrate 401, and an oxide 403 is formed on the surface of the gate line 402 by an anode-oxidation method if occasion demands. Thereafter, a gate insulating film 404 is formed, a semiconductor channel region 405, a drain region 406 and a source region ~~[[404]]~~ 407 are formed, and then a data line 408 is formed (see Fig. 5(A)). Subsequently, an insulating ~~flatting~~ flattening film 409 of polyimide or the like is formed, and an electrode hole is formed in the insulating ~~flatting~~ flattening film. Thereafter, a transparent conductive film 410 is formed at the front surface, and a photoresist is coated on the front surface (see Fig. 5(B)). The same method as the conventional TFT producing method is used for these processes.